

# PBSS5350D

# 50 V, 3 A PNP low VCEsat (BISS) transistor Rev. 6 — 28 June 2011

**Product data sheet** 

#### **Product profile** 1.

### 1.1 General description

PNP low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4350D

#### 1.2 Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High current capability
- High efficiency due to less heat generation
- AEC-Q101 qualified
- Smaller Printed-Circuit Board (PCB) area than for conventional transistors

### 1.3 Applications

- Supply line switching circuits
- Battery management applications
- DC-to-DC conversion

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-50	V
I <sub>C</sub>	collector current		-	-	-3	Α
I <sub>CM</sub>	peak collector current		-	-	-5	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C = -2 \text{ A}$ ; $I_B = -200 \text{ mA}$ ; pulsed; $t_p \le 300 \text{ µs}$ ; $\delta \le 0.02$ ; $T_{amb} = 25 \text{ °C}$	-	120	150	mΩ



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# 2. Pinning information

### Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	С	collector	D. D. D.	
2	С	collector	<u> </u>	1, 2, 5, 6 
3	В	base		3 —
4	Е	emitter	1 12 13	ì
5	С	collector	SOT457 (TSOP6)	4 sym030
6	С	collector		3,

# 3. Ordering information

### Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS5350D	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457

### 4. Marking

### Table 4. Marking codes

Type number	Marking code
PBSS5350D	53

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### 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	-60	V
$V_{CEO}$	collector-emitter voltage	open base		-	-50	V
$V_{EBO}$	emitter-base voltage	open collector		-	-6	V
I <sub>C</sub>	collector current			-	-3	Α
I <sub>CM</sub>	peak collector current			-	-5	Α
I <sub>BM</sub>	peak base current			-	-1	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	<u>[1]</u>	-	600	mW
			[2]	-	750	mW
			[3]	-	1200	mW
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance	in free air	<u>[1]</u>	-	-	208	K/W
from junction to ambient		[2]	-	-	160	K/W	
	ambient	pulsed; $t_p \le 50$ ms; $\delta \le 0.5$ .; in free air	[2]	-	-	100	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

<sup>[3]</sup> Device mounted on an FR4 4-layer PCB.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

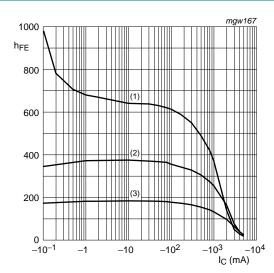
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# 7. Characteristics

### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = -50 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nΑ
	current	V <sub>CB</sub> = -50 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; $I_{C}$ = -500 mA; $T_{amb}$ = 25 °C	200	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -1 A; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb}$ = 25 °C	200	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -2 A; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb}$ = 25 °C	100	-	-	
V <sub>CEsat</sub>	collector-emitter	$I_C$ = -500 mA; $I_B$ = -50 mA; $T_{amb}$ = 25 °C	-	-	-100	mV
	saturation voltage	$I_C = -1 \text{ A}; I_B = -50 \text{ mA}; T_{amb} = 25 \text{ °C}$	-	-	-180	mV
		$I_C = -2 \text{ A}$ ; $I_B = -200 \text{ mA}$ ; pulsed;	-	-	-300	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$t_p \le 300 \text{ μs; } δ \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	-	120	150	mΩ
$V_{BEsat}$	base-emitter saturation voltage		-	-	-1.2	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V; } I_{C} = -1 \text{ A; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	-	-	-1.1	V
f <sub>T</sub>	transition frequency	$V_{CE}$ = -5 V; $I_{C}$ = -100 mA; f = 100 MHz; $T_{amb}$ = 25 °C	100	-	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$	-	-	40	pF

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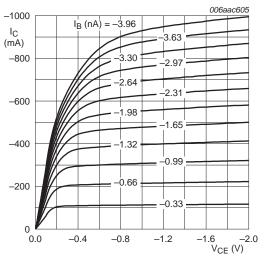
 $V_{CE} = -2 V$ 

(1)  $T_{amb} = 150 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -55$  °C

Fig 1. DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$ 

Fig 2. Collector current as a function of collector-emitter voltage; typical values

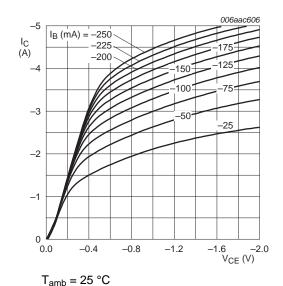
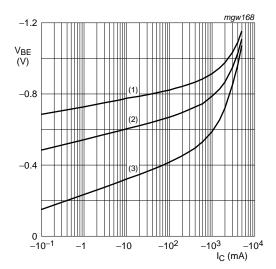


Fig 3. Collector current as a function of collector-emitter voltage; typical values



 $V_{CE} = -2 V$ 

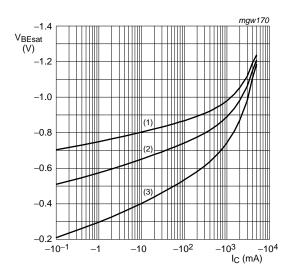
(1)  $T_{amb} = -55 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 150 \, ^{\circ}C$ 

Fig 4. Base-emitter voltage as a function of collector current; typical values

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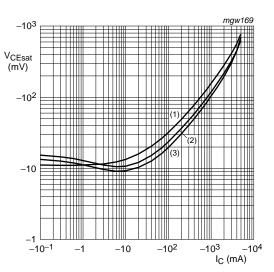
$$I_{\rm C}/I_{\rm B} = 10$$

(1) 
$$T_{amb} = -55$$
 °C

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 5. Base-emitter saturation voltage as a function of collector current; typical values



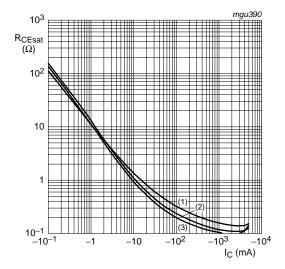
$$I_{\rm C}/I_{\rm B}=10$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55$$
 °C

Fig 6. Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 7. Collector-emitter saturation resistance as a function of collector current; typical values

# 8. Package outline

# Plastic surface-mounted package (TSOP6); 6 leads **SOT457** В = v M A pin 1 index 3 ⊕ w (M) B detail X **DIMENSIONS** (mm are the original dimensions) UNIT Е Q Lp 0.40 3.1 0.26 1.7 3.0 0.6 0.33 0.95 0.2 0.2 0.1 mm 0.013 0.25 0.10

OUTLINE	REFER		REFERENCES		EUROPEAN	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT457			SC-74			<del>-05-11-07-</del> 06-03-16

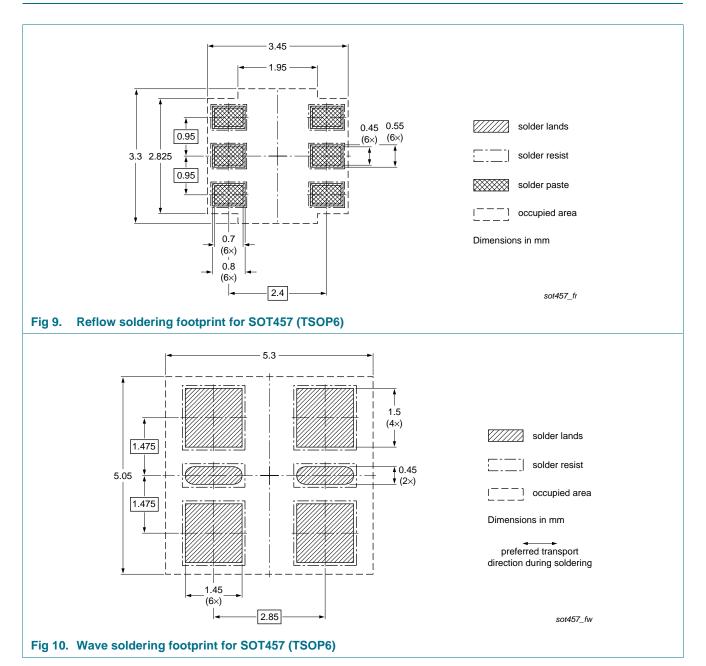
Fig 8. Package outline SOT457 (TSOP6)

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# 9. Soldering



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# 10. Revision history

### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5350D v.6	20110628	Product data sheet	-	PBSS5350D v.5
Modifications:	<ul> <li>5 "Limiting values"</li> </ul>	: P <sub>tot</sub> conditions updated.		
PBSS5350D v.5	20110323	Product data sheet	-	PBSS5350D v.4
PBSS5350D v.4	20011113	Product specification	-	PBSS5350D v.3
PBSS5350D v.3	20010713	Product specification	-	PBSS5350D v.2
PBSS5350D v.2	20010126	Product specification	-	PBSS5350D v.1
PBSS5350D v.1	20000308	Product specification	-	-

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Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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